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Dual-bit, dual-supply voltage level translator/transceiver; 3-state

Rev. 7 — 8 February 2013

Product data sheet

1. General description

The 74AVC2T45 is a dual-bit, dual-supply transceiver that enables bidirectional level translation. It features two data input-output ports (nA and nB), a direction control input (DIR) and dual-supply pins ($V_{CC(A)}$ and $V_{CC(B)}$). Both $V_{CC(A)}$ and $V_{CC(B)}$ can be supplied at any voltage between 0.8 V and 3.6 V making the device suitable for translating between any of the low voltage nodes (0.8 V, 1.2 V, 1.5 V, 1.8 V, 2.5 V and 3.3 V). Pins nA and DIR are referenced to $V_{CC(A)}$ and pins nB are referenced to $V_{CC(B)}$. A HIGH on DIR allows transmission from nA to nB and a LOW on DIR allows transmission from nB to nA.

The device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing any damaging backflow current through the device when it is powered down. In Suspend mode when either $V_{CC(A)}$ or $V_{CC(B)}$ are at GND level, both A and B are in the high-impedance OFF-state.

2. Features and benefits

- Wide supply voltage range:
 - ◆ V_{CC(A)}: 0.8 V to 3.6 V
 - ◆ V_{CC(B)}: 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3B exceeds 8000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101C exceeds 1000 V
- Maximum data rates:
 - 500 Mbit/s (1.8 V to 3.3 V translation)
 - 320 Mbit/s (<1.8 V to 3.3 V translation)
 - 320 Mbit/s (translate to 2.5 V or 1.8 V)
 - 280 Mbit/s (translate to 1.5 V)
 - 240 Mbit/s (translate to 1.2 V)
- Suspend mode
- Latch-up performance exceeds 100 mA per JESD 78 Class II



- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

3. Ordering information

Table 1.Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AVC2T45DP	-40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74AVC2T45DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74AVC2T45GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 \times 1.95 \times 0.5 mm	SOT833-1
74AVC2T45GF	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1 \times 0.5$ mm	SOT1089
74AVC2T45GD	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body $3\times2\times0.5~\text{mm}$	SOT996-2
74AVC2T45GN	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.2 \times 1.0 \times 0.35$ mm	SOT1116
74AVC2T45GS	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1.0 \times 0.35$ mm	SOT1203

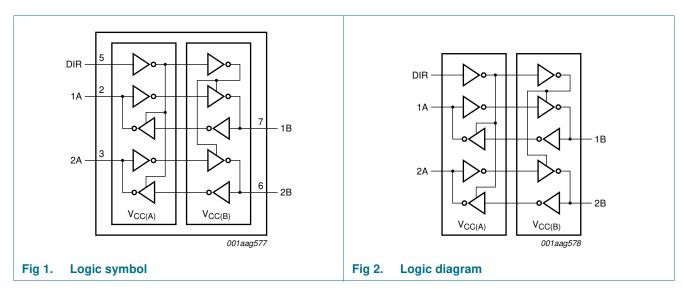
4. Marking

Table 2. Marking	
Type number	Marking code ^[1]
74AVC2T45DP	B45
74AVC2T45DC	B45
74AVC2T45GT	B45
74AVC2T45GF	B5
74AVC2T45GD	B45
74AVC2T45GN	B5
74AVC2T45GS	B5

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

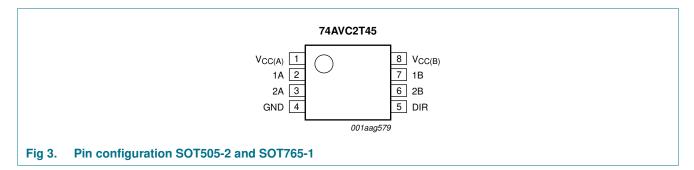
Dual-bit, dual-supply voltage level translator/transceiver; 3-state

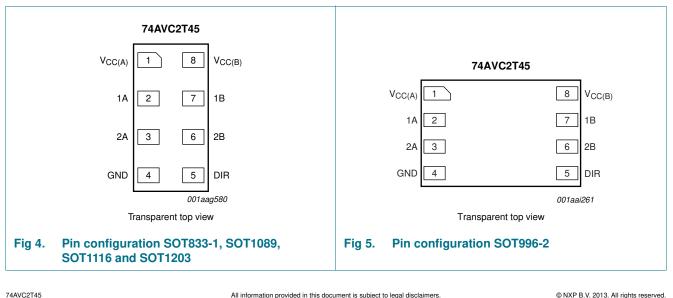
Functional diagram 5.



Pinning information 6.

6.1 Pinning





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6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
V _{CC(A)}	1	supply voltage A (referenced to pins 1A, 2A and DIR)
1A	2	data input or output
2A	3	data input or output
GND	4	ground (0 V)
DIR	5	direction control
2B	6	data input or output
1B	7	data input or output
V _{CC(B)}	8	supply voltage B (referenced to pins 1B and 2B)

7. Functional description

Table 4. Function table^[1]

Supply voltage	Input	Input/output ^[2]	Input/output ^[2]			
V _{CC(A)} , V _{CC(B)}	DIR ^[3]	nA	nB			
0.8 V to 3.6 V	L	nA = nB	input			
0.8 V to 3.6 V	Н	input	nB = nA			
GND ^[4]	Х	Z	Z			

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

[2] The input circuit of the data I/O is always active.

 $\label{eq:constraint} [3] \quad \mbox{The DIR input circuit is referenced to $V_{CC(A)}$}.$

Dual-bit, dual-supply voltage level translator/transceiver; 3-state

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

			0	.0	,
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC(A)}	supply voltage A		-0.5	+4.6	V
V _{CC(B)}	supply voltage B		-0.5	+4.6	V
I _{IK}	input clamping current	V ₁ < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode	<u>[1][2][3]</u> _0.5	$V_{CCO} + 0.5$	V
		Suspend or 3-state mode	<u>[1]</u> –0.5	+4.6	V
lo	output current	$V_{O} = 0 V$ to V_{CCO}	-	±50	mA
I _{CC}	supply current	$I_{CC(A)}$ or $I_{CC(B)}$	-	100	mA
I _{GND}	ground current		-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to \ +125 \ ^{\circ}C$	<u>[4]</u> _	250	mW

[1] The minimum input voltage rating and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] V_{CCO} is the supply voltage associated with the output port.

[3] V_{CCO} + 0.5 V should not exceed 4.6 V.

[4] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly at 2.5 mW/K. For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K. For XSON8 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Parameter	Conditions	Min	Max	Unit
supply voltage A		0.8	3.6	V
supply voltage B		0.8	3.6	V
input voltage		0	3.6	V
output voltage	Active mode	<u>[1]</u> 0	V _{CCO}	V
	Suspend or 3-state mode	0	3.6	V
ambient temperature		-40	+125	°C
input transition rise and fall rate	$V_{CCI} = 0.8 V \text{ to } 3.6 V$	[2] _	5	ns/V
	supply voltage A supply voltage B input voltage output voltage ambient temperature	supply voltage A supply voltage B input voltage output voltage Active mode Suspend or 3-state mode ambient temperature	supply voltage A 0.8 supply voltage B 0.8 input voltage 0 output voltage 11 0 Suspend or 3-state mode 0 ambient temperature -40	supply voltage A0.83.6supply voltage B0.83.6input voltage03.6output voltage03.6Suspend or 3-state mode10V _{CCO} Suspend or 3-state mode03.6ambient temperature-40+125

[1] V_{CCO} is the supply voltage associated with the output port.

[2] V_{CCI} is the supply voltage associated with the input port.

10. Static characteristics

Table 7. Typical static characteristics at $T_{amb} = 25 \ ^{\circ}C^{[1][2]}$

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

	1 0					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O} = -1.5 \text{ mA}; \ V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V}$	-	0.69	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O} = 1.5 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V}$	-	0.07	-	V
l _l	input leakage current	DIR input; $V_I = 0 V \text{ or } 3.6 V$; $V_{CC(A)} = V_{CC(B)} = 0.8 V \text{ to } 3.6 V$	-	±0.025	±0.25	μA
I _{OZ}	OFF-state output current	A or B port; $V_O = 0$ V or V_{CCO} ; $V_{CC(A)} = V_{CC(B)} = 0.8$ V to 3.6 V	[3] _	±0.5	±2.5	μA
I _{OFF}	power-off leakage current	A port; V ₁ or V _O = 0 V to 3.6 V; V _{CC(A)} = 0 V; V _{CC(B)} = 0.8 V to 3.6 V	-	±0.1	±1	μA
		B port; V _I or V _O = 0 V to 3.6 V; V _{CC(B)} = 0 V; V _{CC(A)} = 0.8 V to 3.6 V	-	±0.1	±1	μA
CI	input capacitance	DIR input; $V_I = 0 V \text{ or } 3.3 V$; $V_{CC(A)} = V_{CC(B)} = 3.3 V$	-	1.0	-	рF
C _{I/O}	input/output capacitance	A and B port; Suspend mode; $V_O = V_{CCO}$ or GND; $V_{CC(A)} = V_{CC(B)} = 3.3 \text{ V}$	-	4.0	-	рF

[1] V_{CCO} is the supply voltage associated with the output port.

 $\label{eq:VCCI} \ensuremath{\left[2\right]} \quad V_{CCI} \ensuremath{\text{ is the supply voltage associated with the data input port.}$

[3] For I/O ports, the parameter I_{OZ} includes the input leakage current.

Table 8. Static characteristics [1][2]

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C to	+85 °C	–40 °C to	+125 °C	Unit
			Min	Max	Min	Max	
	HIGH-level	data input					
	input voltage	$V_{CCI} = 0.8 V$	0.70V _{CCI}	-	0.70V _{CCI}	-	V
		V _{CCI} = 1.1 V to 1.95 V	0.65V _{CCI}	-	0.65V _{CCI}	-	V
		$V_{CCI} = 2.3 \text{ V} \text{ to } 2.7 \text{ V}$	1.6	-	1.6	-	V
		$V_{CCI} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2	-	2	-	V
		DIR input					
		$V_{CC(A)} = 0.8 V$	0.70V _{CC(A)}	-	0.70V _{CC(A)}	-	V
		$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}$	$0.65V_{CC(A)}$	-	0.65V _{CC(A)}	-	V
		$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	1.6	-	V
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}$	2	-	2	-	V

NXP Semiconductors

74AVC2T45

Dual-bit, dual-supply voltage level translator/transceiver; 3-state

Symbol	Parameter	Conditions	−40 °C t	o +85 °C	-40 °C to	Unit	
			Min	Max	Min	Max	
VIL	LOW-level	data input			1		
	input voltage	$V_{CCI} = 0.8 V$	-	0.30V _{CCI}	-	0.30V _{CCI}	V
		V _{CCI} = 1.1 V to 1.95 V	-	$0.35V_{CCI}$	-	0.35V _{CCI}	٧
		$V_{CCI} = 2.3 \text{ V} \text{ to } 2.7 \text{ V}$	-	0.7	-	0.7	V
		$V_{CCI} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	0.9	-	0.9	V
		DIR input					
		$V_{CC(A)} = 0.8 V$	-	0.30V _{CC(A)}	-	0.30V _{CC(A)}	V
		V _{CC(A)} = 1.1 V to 1.95 V	-	0.35V _{CC(A)}	-	0.35V _{CC(A)}	V
		$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}$	-	0.7	-	0.7	V
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}$	-	0.9	-	0.9	V
√ _{ОН}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$					
	output voltage	$I_{O} = -100 \ \mu A;$ $V_{CC(A)} = V_{CC(B)} = 0.8 \ V \text{ to } 3.6 \ V$	$V_{\text{CCO}} - 0.1$	-	$V_{\text{CCO}}-0.1$	-	V
		$I_O = -3 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.1 \text{ V}$	0.85	-	0.85	-	V
		$I_{O} = -6 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$	1.05	-	1.05	-	V
		$I_{O} = -8 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.65 \text{ V}$	1.2	-	1.2	-	V
		$I_O = -9 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$	1.75	-	1.75	-	V
		$I_{O} = -12 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$	2.3	-	2.3	-	V
/ _{OL}	LOW-level output voltage output voltage input leakage current OFF-state output current	$V_{I} = V_{IH} \text{ or } V_{IL}$					
	output voltage	$I_{O} = 100 \ \mu A;$ $V_{CC(A)} = V_{CC(B)} = 0.8 \ V \text{ to } 3.6 \ V$	-	0.1	-	0.1	V
		$I_{O} = 3 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.1 \text{ V}$	-	0.25	-	0.25	V
		$I_{O} = 6 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$	-	0.35	-	0.35	V
		I_{O} = 8 mA; $V_{CC(A)}$ = $V_{CC(B)}$ = 1.65 V	-	0.45	-	0.45	V
		$I_{O} = 9 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$	-	0.55	-	0.55	V
		$I_{O} = 12 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$	-	0.7	-	0.7	V
l		DIR input; $V_I = 0 V \text{ or } 3.6 V$; $V_{CC(A)} = V_{CC(B)} = 0.8 V \text{ to } 3.6 V$	-	±1	-	±1.5	μA
OZ		A or B port; $V_O = 0$ V or V_{CCO} ; $V_{CC(A)} = V_{CC(B)} = 3.6$ V	[3] _	±5	-	±7.5	μA
OFF	power-off leakage	A port; V ₁ or V _O = 0 V to 3.6 V; V _{CC(A)} = 0 V; V _{CC(B)} = 0.8 V to 3.6 V	-	±5	-	±35	μA
	current	$ B \text{ port; } V_1 \text{ or } V_O = 0 \text{ V to } 3.6 \text{ V; } \\ V_{CC(B)} = 0 \text{ V; } V_{CC(A)} = 0.8 \text{ V to } 3.6 \text{ V } $	-	±5	-	±35	μA

Table 8. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Dual-bit, dual-supply voltage level translator/transceiver; 3-state

Table 8. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to	o +85 °C	-40 °C to	+125 °C	Unit
			Min	Max	Min	Max	
I _{CC}	supply current	A port; $V_I = 0$ V or V_{CCI} ; $I_O = 0$ A					
		$V_{CC(A)} = 0.8 V \text{ to } 3.6 V;$ $V_{CC(B)} = 0.8 V \text{ to } 3.6 V$	-	8	-	11.5	μA
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$	-	8	-	11.5	μA
		$V_{CC(A)} = 0 V; V_{CC(B)} = 3.6 V$	-2	-	-8	-	μA
		B port; $V_I = 0$ V or V_{CCI} ; $I_O = 0$ A					
			$V_{CC(A)} = 0.8 V \text{ to } 3.6 V;$ $V_{CC(B)} = 0.8 V \text{ to } 3.6 V$	-	8	-	11.5
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$	-2	-	-8	-	μA
		$V_{CC(A)} = 0 V; V_{CC(B)} = 3.6 V$	-	8	-	11.5	μA
		A plus B port ($I_{CC(A)} + I_{CC(B)}$); $I_O = 0 A$; $V_I = 0 V \text{ or } V_{CCI}$; $V_{CC(A)} = 0.8 V \text{ to } 3.6 V$; $V_{CC(B)} = 0.8 V \text{ to } 3.6 V$	-	16	-	23	μA

[1] V_{CCO} is the supply voltage associated with the output port.

 $\label{eq:VCCI} \ensuremath{\left[2\right]} \quad V_{CCI} \ensuremath{\text{ is the supply voltage associated with the data input port.}$

[3] For I/O ports, the parameter I_{OZ} includes the input leakage current.

11. Dynamic characteristics

Table 9. Typical dynamic characteristics at $V_{CC(A)} = 0.8$ V and $T_{amb} = 25 \circ C$ [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8; for wave forms see Figure 6 and Figure 7

Symbol	Parameter	Parameter Conditions V _{CC(B)}							Unit
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
t _{pd}	propagation delay	A to B	15.5	8.1	7.6	7.7	8.4	9.2	ns
		B to A	15.5	12.7	12.3	12.2	12.0	11.8	ns
t _{dis}	disable time	DIR to A	12.2	12.2	12.2	12.2	12.2	12.2	ns
		DIR to B	11.7	7.9	7.6	8.2	8.7	10.2	ns
t _{en}	enable time	DIR to A	27.2	20.6	19.9	20.4	20.7	22.0	ns
		DIR to B	27.7	20.3	19.8	19.9	20.6	21.4	ns

[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} . t_{en} is a calculated value using the formula shown in Section 13.4 "Enable times"

Table 10. Typical dynamic characteristics at $V_{CC(B)} = 0.8$ V and $T_{amb} = 25 \circ C$ [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see <u>Figure 8</u>; for wave forms see <u>Figure 6</u> and <u>Figure 7</u>

Symbol	Parameter	Conditions	V _{CC(A)}						Unit
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
t _{pd}	propagation delay	A to B	15.5	12.7	12.3	12.2	12.0	11.8	ns
		B to A	15.5	8.1	7.6	7.7	8.4	9.2	ns
t _{dis}	disable time	DIR to A	12.2	4.9	3.8	3.7	2.8	3.4	ns
		DIR to B	11.7	9.2	9.0	8.8	8.7	8.6	ns
t _{en}	enable time	DIR to A	27.2	17.3	16.6	16.5	17.1	17.8	ns
		DIR to B	27.7	17.6	16.1	15.9	14.8	15.2	ns

[1] t_{pd} is the same as t_{PLH} and t_{PHL}; t_{dis} is the same as t_{PLZ} and t_{PHZ}; t_{en} is the same as t_{PZL} and t_{PZH}. t_{en} is a calculated value using the formula shown in <u>Section 13.4 "Enable times"</u>

Table 11.	Typical power dissipation capacitance at $V_{CC(A)} = V_{CC(B)}$ and $T_{amb} = 25 \ ^{\circ}C \ \frac{[1][2]}{C}$
Voltages a	re referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions			V _{CC(A)} ar	nd V _{CC(B)}			Unit
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
C _{PD}	power dissipation capacitance	A port: (direction A to B); B port: (direction B to A)	1	2	2	2	2	2	pF
		A port: (direction B to A); B port: (direction A to B)	9	11	11	12	14	17	pF

[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}{}^2 \times f_o)$ = sum of the outputs.

[2] $f_i = 10 \text{ MHz}$; $V_I = \text{GND}$ to V_{CC} ; $t_r = t_f = 1 \text{ ns}$; $C_L = 0 \text{ pF}$; $R_L = \infty \Omega$.

NXP Semiconductors

74AVC2T45

Dual-bit, dual-supply voltage level translator/transceiver; 3-state

Symbol F	Parameter	Conditions	V _{CC(B)}								Unit		
				± 0.1 V	1.5 V	± 0.1 V	1.8 V ±	0.15 V	2.5 V	± 0.2 V	3.3 V	± 0.3 V	
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	-
$V_{CC(A)} =$	1.1 V to 1.3 V												
t _{pd} propagation	A to B	1.0	9.0	0.7	6.8	0.6	6.1	0.5	5.7	0.5	6.1	ns	
	delay	B to A	1.0	9.0	0.8	8.0	0.7	7.7	0.6	7.2	0.5	7.1	ns
t _{dis}	disable time	DIR to A	2.2	8.8	2.2	8.8	2.2	8.8	2.2	8.8	2.2	8.8	ns
		DIR to B	2.2	8.4	1.8	6.7	2.0	6.9	1.7	6.2	2.4	7.2	ns
t _{en}	enable time	DIR to A	-	17.4	-	14.7	-	14.6	-	13.4	-	14.3	ns
		DIR to B	-	17.8	-	15.6	-	14.9	-	14.5	-	14.9	ns
$V_{CC(A)} =$	1.4 V to 1.6 V												
t _{pd}	propagation	A to B	1.0	8.0	0.7	5.4	0.6	4.6	0.5	3.7	0.5	3.5	ns
	delay	B to A	1.0	6.8	0.8	5.4	0.7	5.1	0.6	4.7	0.5	4.5	ns
t _{dis}	disable time	DIR to A	1.6	6.3	1.6	6.3	1.6	6.3	1.6	6.3	1.6	6.3	ns
		DIR to B	2.0	7.6	1.8	5.9	1.6	6.0	1.2	4.8	1.7	5.5	ns
t _{en}	enable time	DIR to A	-	14.4	-	11.3	-	11.1	-	9.5	-	10.0	ns
		DIR to B	-	14.3	-	11.7	-	10.9	-	10.0	-	9.8	ns
$V_{CC(A)} =$	1.65 V to 1.95	V											
t _{pd}	propagation	A to B	1.0	7.7	0.6	5.1	0.5	4.3	0.5	3.4	0.5	3.1	ns
1	delay	B to A	1.0	6.1	0.7	4.6	0.5	4.4	0.5	3.9	0.5	3.7	ns
t _{dis}	disable time	DIR to A	1.6	5.5	1.6	5.5	1.6	5.5	1.6	5.5	1.6	5.5	ns
		DIR to B	1.8	7.7	1.8	5.7	1.4	5.8	1.0	4.5	1.5	5.2	ns
t _{en}	enable time	DIR to A	-	13.8	-	10.3	-	10.2	-	8.4	-	8.9	ns
0.1		DIR to B	-	13.2	-	10.6	-	9.8	-	8.9	-	8.6	ns
$V_{CC(A)} = $	2.3 V to 2.7 V												
t _{pd}	propagation	A to B	1.0	7.2	0.5	4.7	0.5	3.9	0.5	3.0	0.5	2.6	ns
20	delay	B to A	1.0	5.7	0.6	3.8	0.5	3.4	0.5	3.0	0.5	2.8	ns
t _{dis}	disable time	DIR to A	1.5	4.2	1.5	4.2	1.5	4.2	1.5	4.2	1.5	4.2	ns
dio		DIR to B	1.7	7.3	2.0	5.2	1.5	5.1	0.6	4.2	1.1	4.8	ns
t _{en}	enable time	DIR to A	-	13.0	-	9.0	-	8.5	_	7.2	-	7.6	ns
-011		DIR to B	-	11.4	-	8.9	-	8.1	_	7.2	-	6.8	ns
$V_{CC(A)} = $	3.0 V to 3.6 V							-					
t _{pd}	propagation	A to B	1.0	7.1	0.5	4.5	0.5	3.7	0.5	2.8	0.5	2.4	ns
μα	delay	B to A	1.0	6.1	0.6	3.6	0.5	3.1	0.5	2.6	0.5	2.4	ns
t _{dis}	disable time	DIR to A	1.5	4.7	1.5	4.7	1.5	4.7	1.5	4.7	1.5	4.7	ns
-013		DIR to B	1.7	7.2	0.7	5.5	0.6	5.5	0.7	4.1	1.7	4.7	ns
t _{en}	enable time	DIR to A	-	13.3	-	9.1	-	8.6	-	6.7	-	7.1	ns
-611		DIR to B	-	11.8	-	9.2	-	8.4	-	7.5	-	7.1	ns

Table 12. Dynamic characteristics for temperature range –40 °C to +85 °C [1]

 $[1] \quad t_{pd} \text{ is the same as } t_{PLH} \text{ and } t_{PHL}; \\ t_{dis} \text{ is the same as } t_{PLZ} \text{ and } t_{PHZ}; \\ t_{en} \text{ is the same as } t_{PZL} \text{ and } t_{PZH}. \\ t_{en} \text{ is a calculated value using the formula shown in } \underline{Section 13.4 "Enable times"}$

NXP Semiconductors

74AVC2T45

Dual-bit, dual-supply voltage level translator/transceiver; 3-state

Symbol	Parameter	Conditions	V _{CC(B)}								Unit		
				± 0.1 V	1.5 V	± 0.1 V	1.8 V ±	± 0.15 V	2.5 V	± 0.2 V	3.3 V	± 0.3 V	
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	-
V _{CC(A)} =	1.1 V to 1.3 V	1											
t _{pd} propagation delay	A to B	1.0	9.9	0.7	7.5	0.6	6.8	0.5	6.3	0.5	6.8	ns	
	B to A	1.0	9.9	0.8	8.8	0.7	8.5	0.6	8.0	0.5	7.9	ns	
t _{dis} disable time	DIR to A	2.2	9.7	2.2	9.7	2.2	9.7	2.2	9.7	2.2	9.7	ns	
		DIR to B	2.2	9.2	1.8	7.4	2.0	7.6	1.7	6.9	2.4	8.0	ns
t _{en}	enable time	DIR to A	-	19.1	-	16.2	-	16.1	-	14.9	-	15.9	ns
		DIR to B	-	19.6	-	17.2	-	16.5	-	16.0	-	16.5	ns
$V_{CC(A)} =$	1.4 V to 1.6 V												
t _{pd} propagation	A to B	1.0	8.8	0.7	6.0	0.6	5.1	0.5	4.1	0.5	3.9	ns	
	delay	B to A	1.0	7.5	0.8	6.0	0.7	5.7	0.6	5.2	0.5	5.0	ns
t _{dis}	disable time	DIR to A	1.6	7.0	1.6	7.0	1.6	7.0	1.6	7.0	1.6	7.0	ns
		DIR to B	2.0	8.3	1.8	6.5	1.6	6.6	1.2	5.3	1.7	6.1	ns
t _{en}	enable time	DIR to A	-	15.8	-	12.5	-	12.3	-	10.5	-	11.1	ns
		DIR to B	-	15.8	-	13.0	-	12.1	-	11.1	-	10.9	ns
$V_{CC(A)} =$	1.65 V to 1.95	V											
t _{pd}	propagation	A to B	1.0	8.5	0.6	5.7	0.5	4.8	0.5	3.8	0.5	3.5	ns
	delay	B to A	1.0	6.8	0.7	5.1	0.5	4.9	0.5	4.3	0.5	4.1	ns
t _{dis}	disable time	DIR to A	1.6	6.1	1.6	6.1	1.6	6.1	1.6	6.1	1.6	6.1	ns
		DIR to B	1.8	8.5	1.8	6.3	1.4	6.4	1.0	5.0	1.5	5.8	ns
t _{en}	enable time	DIR to A	-	15.3	-	11.4	-	11.3	-	9.3	-	9.9	ns
		DIR to B	-	14.6	-	11.8	-	10.9	-	9.9	-	9.6	ns
$V_{CC(A)} =$	2.3 V to 2.7 V												
t _{pd}	propagation	A to B	1.0	8.0	0.5	5.2	0.5	4.3	0.5	3.3	0.5	2.9	ns
	delay	B to A	1.0	6.3	0.6	4.2	0.5	3.8	0.5	3.3	0.5	3.1	ns
t _{dis}	disable time	DIR to A	1.5	4.7	1.5	4.7	1.5	4.7	1.5	4.7	1.5	4.7	ns
		DIR to B	1.7	8.0	2.0	5.8	1.5	5.7	0.6	4.7	1.1	5.3	ns
t _{en}	enable time	DIR to A	-	14.3	-	10.0	-	9.5	-	8.0	-	8.4	ns
		DIR to B	-	12.7	-	9.9	-	9.0	-	8.0	-	7.6	ns
$V_{CC(A)} =$	3.0 V to 3.6 V												
t _{pd}	propagation	A to B	1.0	7.9	0.5	5.0	0.5	4.1	0.5	3.1	0.5	2.7	ns
	delay	B to A	1.0	6.8	0.6	4.0	0.5	3.5	0.5	2.9	0.5	2.7	ns
t _{dis}	disable time	DIR to A	1.5	5.2	1.5	5.2	1.5	5.2	1.5	5.2	1.5	5.2	ns
2.0		DIR to B	1.7	7.9	0.7	6.1	0.6	6.1	0.7	4.6	1.7	5.2	ns
t _{en}	enable time	DIR to A	-	14.7	-	10.1	-	9.6	_	7.5	-	7.9	ns
		DIR to B		13.1		10.2		9.3		8.3		7.9	-

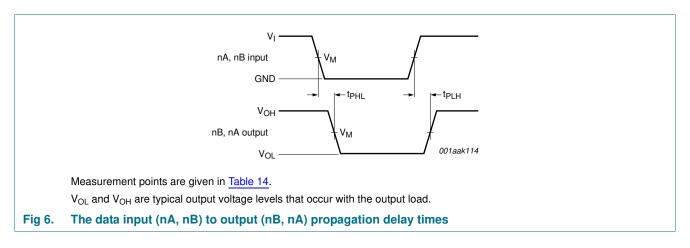
Table 13. Dynamic characteristics for temperature range -40 °C to +125 °C [1]

 $[1] \quad t_{pd} \text{ is the same as } t_{PLH} \text{ and } t_{PHL}; \\ t_{dis} \text{ is the same as } t_{PLZ} \text{ and } t_{PHZ}; \\ t_{en} \text{ is the same as } t_{PZL} \text{ and } t_{PZH}. \\ t_{en} \text{ is a calculated value using the formula shown in } \underline{Section 13.4 "Enable times"}$

74AVC2T45 **Product data sheet**

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12. Waveforms



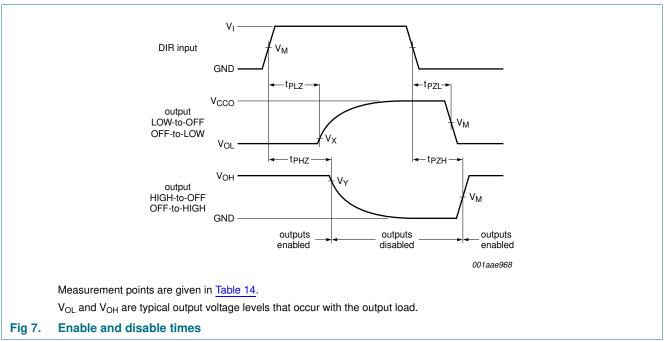


Table 14. Measurement points

Supply voltage	Input ^[1]	Output ^[2]		
V _{CC(A)} , V _{CC(B)}	V _M	V _M	V _X	V _Y
1.1 V to 1.6 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.1 V	V _{OH} – 0.1 V
1.65 V to 2.7 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.15 V	V _{OH} – 0.15 V
3.0 V to 3.6 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.3 V	V _{OH} – 0.3 V

[1] V_{CCI} is the supply voltage associated with the data input port.

[2] V_{CCO} is the supply voltage associated with the output port.

NXP Semiconductors

74AVC2T45

Dual-bit, dual-supply voltage level translator/transceiver; 3-state

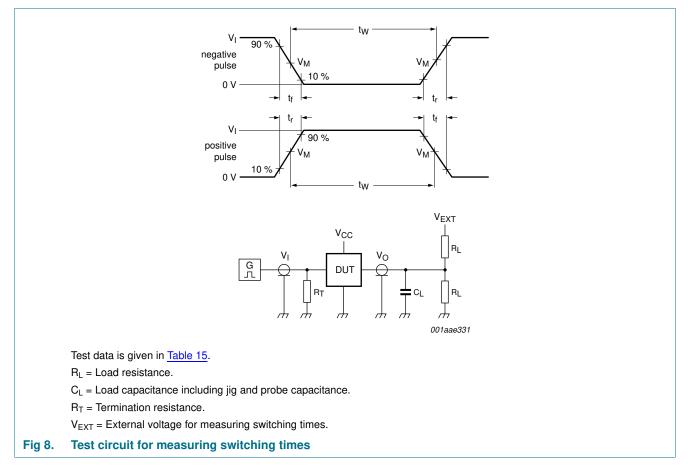


Table 15. Test data

Supply voltage	Input		Load		V _{EXT}		
$V_{CC(A)}, V_{CC(B)}$	V _I [1]	∆t/∆V[2]	CL	RL	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ^[3]}
1.1 V to 1.6 V	V _{CCI}	\leq 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}
1.65 V to 2.7 V	V _{CCI}	\leq 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}
3.0 V to 3.6 V	V _{CCI}	\leq 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}

[1] V_{CCI} is the supply voltage associated with the data input port.

 $[2] \quad dV/dt \geq 1.0 \ V/ns$

[3] V_{CCO} is the supply voltage associated with the output port.

13. Application information

13.1 Unidirectional logic level-shifting application

The circuit given in Figure 9 is an example of the 74AVC2T45 being used in an unidirectional logic level-shifting application.

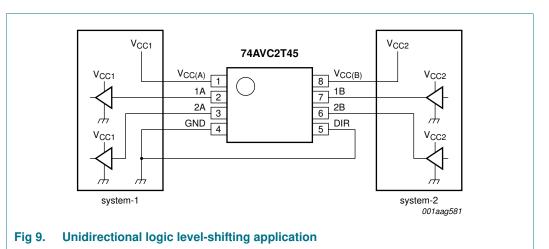


Table 16. Unidirectional logic level-shifting application

		-	
Pin	Name	Function	Description
1	$V_{CC(A)}$	V _{CC1}	supply voltage of system-1 (0.8 V to 3.6 V)
2	1A	OUT1	output level depends on V_{CC1} voltage
3	2A	OUT2	output level depends on V_{CC1} voltage
4	GND	GND	device GND
5	DIR	DIR	the GND (LOW level) determines B port to A port direction
6	2B	IN2	input threshold value depends on V_{CC2} voltage
7	1B	IN1	input threshold value depends on V_{CC2} voltage
8	V _{CC(B)}	V _{CC2}	supply voltage of system-2 (0.8 V to 3.6 V)

14 of 27

13.2 Bidirectional logic level-shifting application

<u>Figure 10</u> shows the 74AVC2T45 being used in a bidirectional logic level-shifting application. Since the device does not have an output enable (OE) pin, the system designer should take precautions to avoid bus contention between system-1 and system-2 when changing directions.

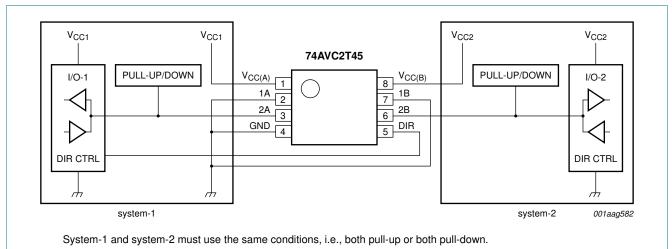


Fig 10. Bidirectional logic level-shifting application

<u>Table 17</u> gives a sequence that will illustrate data transmission from system-1 to system-2 and then from system-2 to system-1.

Table 17. Bidirectional logic level-shifting application

		•		0 11
State	DIR CTRL	I/O-1	I/O-2	Description
1	Н	output	input	system-1 data to system-2
2	Η	Z	Z	system-2 is getting ready to send data to system-1. I/O-1 and I/O-2 are disabled. The bus-line state depends on the pull-up or pull-down.
3	L	Z	Z	DIR bit is set LOW. I/O-1 and I/O-2 still are disabled. The bus-line state depends on the pull-up or pull-down.
4	L	input	output	system-2 data to system-1

[1] System-1 and system-2 must use the same conditions, i.e., both pull-up or both pull-down.

[2] H = HIGH voltage level;

L = LOW voltage level;

Z = high-impedance OFF-state.

13.3 Power-up considerations

The device is designed such that no special power-up sequence is required other than GND being applied first.

V _{CC(A)}	V _{CC(B)}									
	0 V	0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V			
0 V	0	0.1	0.1	0.1	0.1	0.1	0.1	μA		
0.8 V	0.1	0.1	0.1	0.1	0.1	0.7	2.3	μA		
1.2 V	0.1	0.1	0.1	0.1	0.1	0.3	1.4	μA		
1.5 V	0.1	0.1	0.1	0.1	0.1	0.1	0.9	μA		
1.8 V	0.1	0.1	0.1	0.1	0.1	0.1	0.5	μA		
2.5 V	0.1	0.7	0.3	0.1	0.1	0.1	0.1	μA		
3.3 V	0.1	2.3	1.4	0.9	0.5	0.1	0.1	μA		

Table 18. Typical total supply current (I_{CC(A)} + I_{CC(B)})

13.4 Enable times

The enable times for the 74AVC2T45 are calculated from the following formulas:

- t_{en} (DIR to nA) = t_{dis} (DIR to nB) + t_{pd} (nB to nA)
- t_{en} (DIR to nB) = t_{dis} (DIR to nA) + t_{pd} (nA to nB)

In a bidirectional application, these enable times provide the maximum delay from the time the DIR bit is switched until an output is expected. For example, if the 74AVC2T45 initially is transmitting from A to B, then the DIR bit is switched, the B port of the device must be disabled before presenting it with an input. After the B port has been disabled, an input signal applied to it appears on the corresponding A port after the specified propagation delay.

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14. Package outline

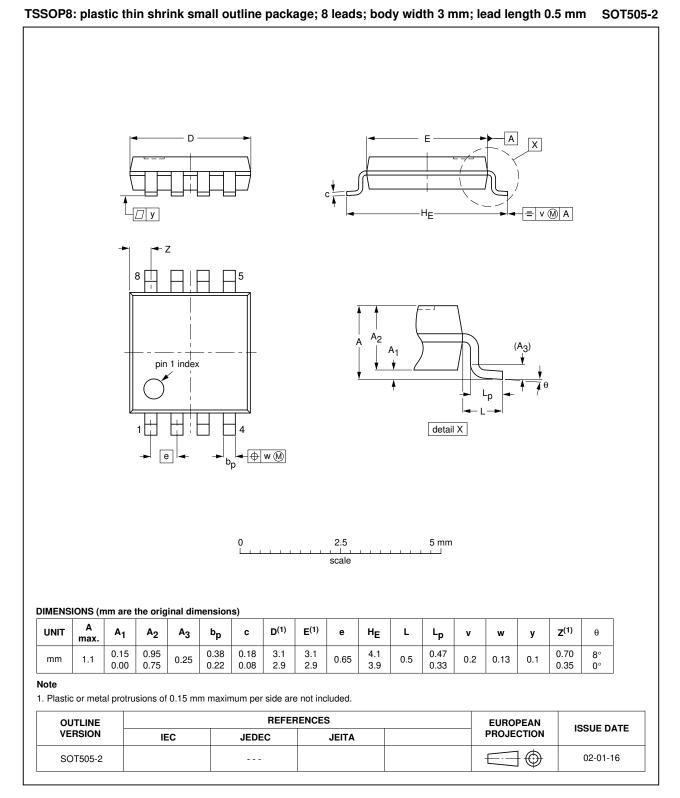


Fig 11. Package outline SOT505-2 (TSSOP8)

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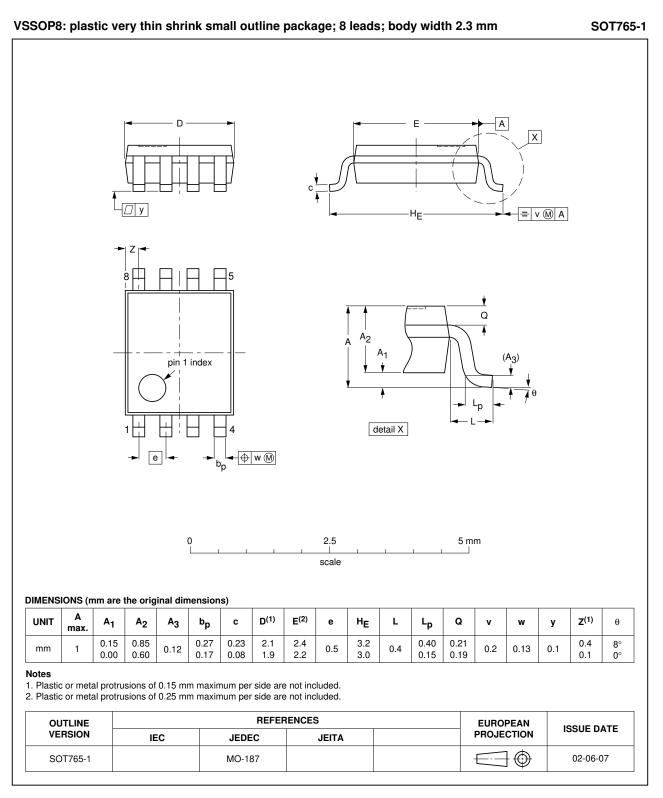


Fig 12. Package outline SOT765-1 (VSSOP8)

74AVC2T45 Product data sheet

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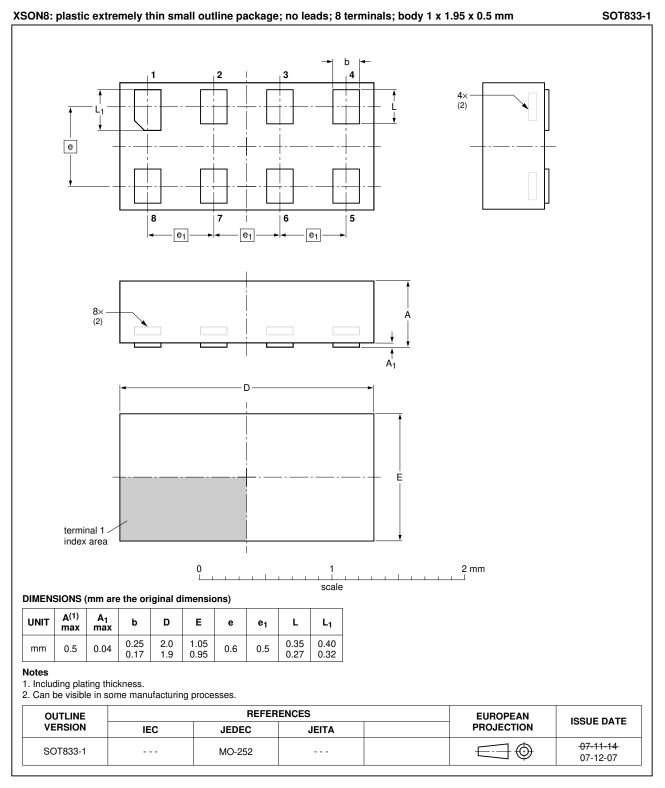
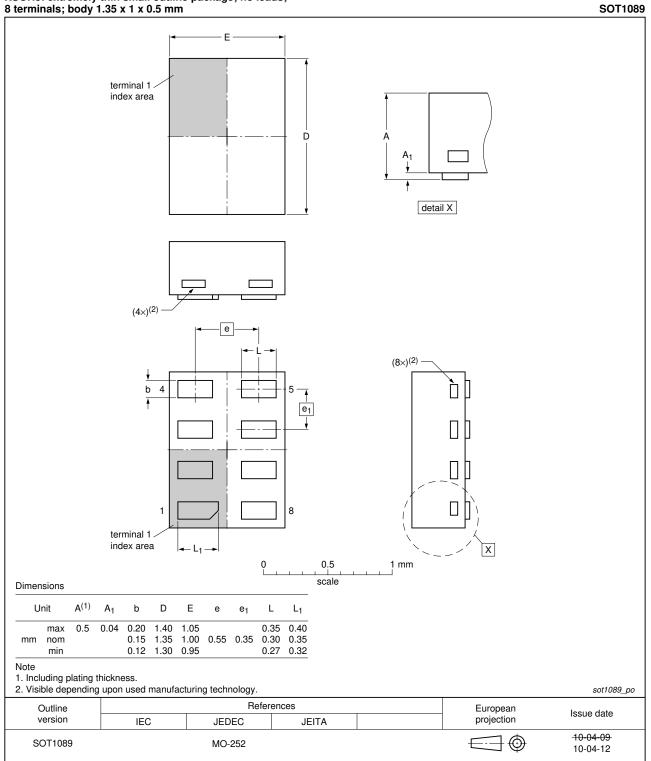


Fig 13. Package outline SOT833-1 (XSON8)

74AVC2T45 Product data sheet

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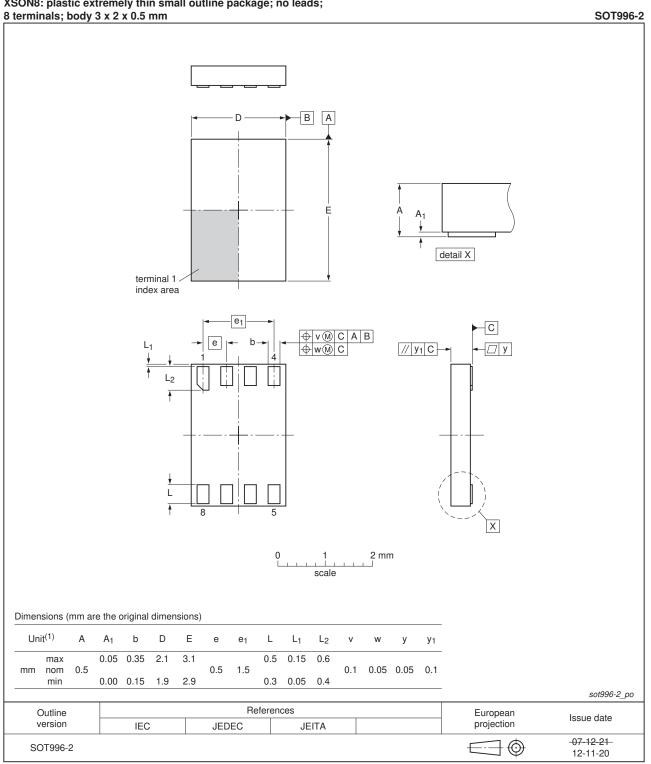


XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1 x 0.5 mm

Fig 14. Package outline SOT1089 (XSON8)

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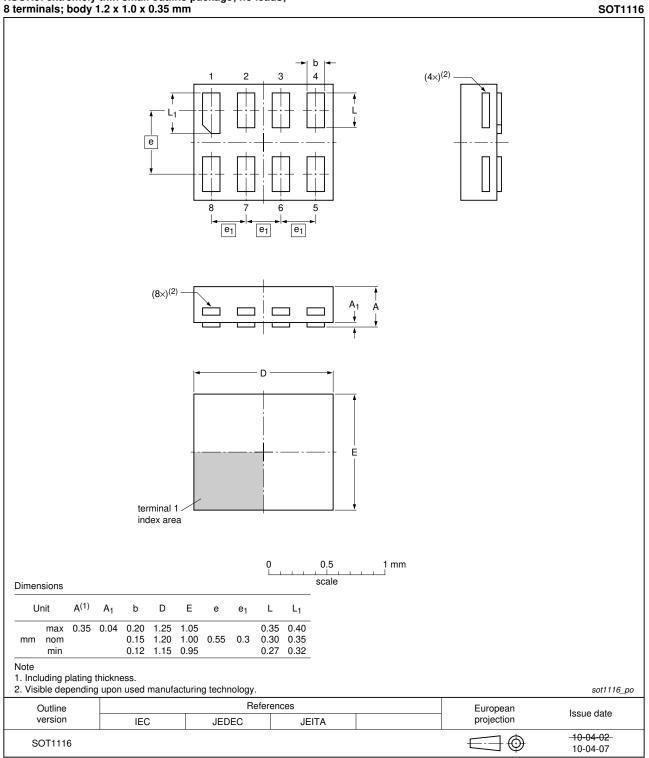


XSON8: plastic extremely thin small outline package; no leads;

Fig 15. Package outline SOT996-2 (XSON8)

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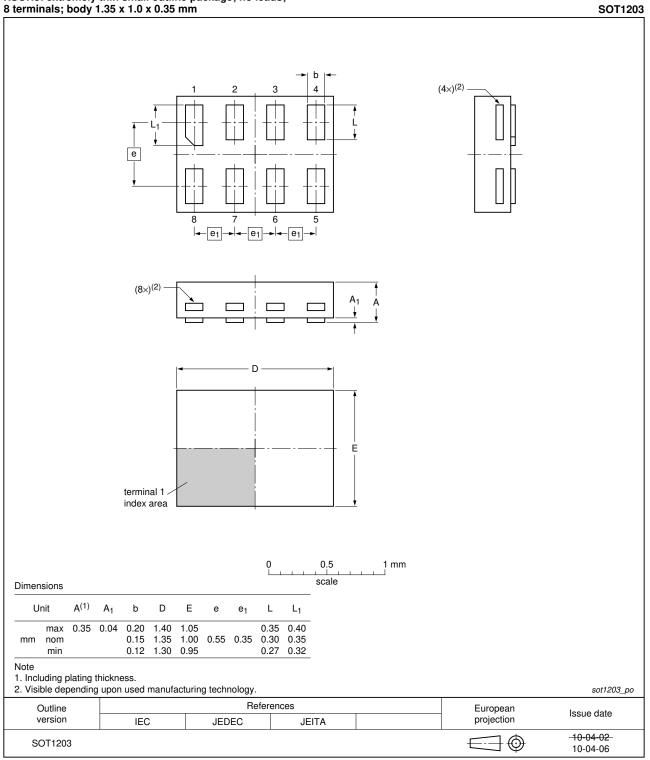


XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.2 x 1.0 x 0.35 mm

Fig 16. Package outline SOT1116 (XSON8)

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Dual-bit, dual-supply voltage level translator/transceiver; 3-state



XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1.0 x 0.35 mm

Fig 17. Package outline SOT1203 (XSON8)

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15. Abbreviations

Table 19.	Abbreviations
Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

16. Revision history

Table 20. Revision hist	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AVC2T45 v.7	20130208	Product data sheet	-	74AVC2T45 v.6
Modifications:	 For type num 	ber 74AVC2T45GD XSON8U	has changed to XSON	18.
74AVC2T45 v.6	20111208	Product data sheet	-	74AVC2T45 v.5
74AVC2T45 v.5	20101130	Product data sheet	-	74AVC2T45 v.4
74AVC2T45 v.4	20090505	Product data sheet	-	74AVC2T45 v.3
74AVC2T45 v.3	20090129	Product data sheet	-	74AVC2T45 v.2
74AVC2T45 v.2	20080620	Product data sheet	-	74AVC2T45 v.1
74AVC2T45 v.1	20070703	Product data sheet	-	-